Appl. No.10/762,599
Paper dated: July 6, 2006 July 6, 2006
Reply to Office Action dated April 6, 2006

Amendments to the Specification:

Please replace the paragraph beginning at page 11, line 17, with the following rewritten paragraph:

-- The alignment marks 30 are arranged on a scribe line for each shot and may use, for example, alignment marks 30A and 30B shown in FIGS. 4 and 5. Reference numeral 30 generalizes reference numerals 30A and 30B. Here, FIGS. 4A and 4B are plane and sectional views of the alignment mark 30A. FIGS. 5A and 5B are plane and sectional views of the alignment mark 30B. In FIGS. 4 and 5, each of the alignment marks 30A and 30B include four mark elements 31A and 31B arranged at regular intervals. A mark element 31 is used as generic term of the mark element 31A and mark element 31B.--

Please replace the paragraph beginning at page 30, line 16, with the following rewritten paragraph:

--Referring now to FIG. 16, a description will be given of a third embodiment according to the present invention. Here, FIG. 16 is an optical path diagram showing principal elements in an overlay inspection apparatus of the third embodiment according to the present invention. The overlay inspection apparatus is one that inspects an overlay state between first and second patterns on a wafer that forms a film on the first pattern, and the second pattern on the film. The illumination light from a light source [[58]] 18 is reflected on a beam splitter [[59]] 19, and passes through a lens [[60]] 20, and illuminates an inspection mark 50 on the wafer 12. The diffracted light from the overlay inspection mark 50 passes through the lens [[60]] 20, the beam splitter [[59]] 19, and the lens [[61]] 21, split by a beam splitter [[62]] 22, and received by area sensors [[63]] 23 and [[64]] 24. The overlay evaluation mark 50 is imaged on the area sensors [[63]] 23 and [[64]] 24 at an imaging magnification of about 100 times. The area sensors [[63]] 23 and [[64]] 24 are used to measure offsets of the overlay inspection mark 50 in directions X and Y, respectively, and arranged at a rotational angle of 90.degree. relative to the optical axis. The wafer 12 is held by the wafer chuck 51, and an XY stage can position a predetermined position on the wafer 12 relative to the detection system 15. Since X and

Y directions adopt the same measurement principle, a description of the positional measurement only in the X direction will be given.--